

NTD5802N, NVD5802N

Power MOSFET

40 V, Single N-Channel, 101 A DPAK

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- MSL 1/260°C
- AEC Q101 Qualified
- 100% Avalanche Tested
- AEC Q101 Qualified – NVD5802N
- These Devices are Pb-Free and are RoHS Compliant

Applications

- CPU Power Delivery
- DC-DC Converters
- Motor Driver

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	40	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current ($R_{\theta JC}$) (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	I_D 101	A
		$T_C = 85^\circ\text{C}$	78	
Power Dissipation ($R_{\theta JC}$) (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	P_D 93.75	W
Continuous Drain Current ($R_{\theta JA}$) (Note 1)		$T_A = 25^\circ\text{C}$	I_D 16.4	A
		$T_A = 85^\circ\text{C}$	12.7	
Power Dissipation ($R_{\theta JA}$) (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D 2.5	W
Pulsed Drain Current		$t_p = 10\mu\text{s}$	$T_A = 25^\circ\text{C}$	I_{DM} 300
Current Limited by Package		$T_A = 25^\circ\text{C}$	$I_{DmaxPkg}$ 45	A
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$	
Source Current (Body Diode)	I_S	50	A	
Drain to Source dV/dt	dV/dt	6.0	V/ns	
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 32\text{ V}, V_{GS} = 10\text{ V}, L = 0.3\text{ mH}, I_{L(pk)} = 40\text{ A}, R_G = 25\ \Omega$)	E_{AS}	240	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$	

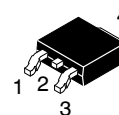
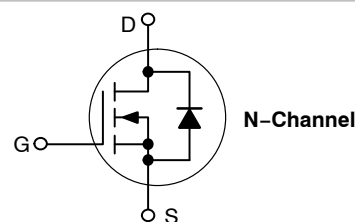
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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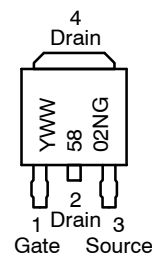
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D
40 V	4.4 m Ω @ 10 V	101 A
	7.8 m Ω @ 5.0 V	50 A



CASE 369C
DPAK
(Bent Lead)
STYLE 2

MARKING DIAGRAMS & PIN ASSIGNMENT



Y = Year
WW = Work Week
5802N = Device Code
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	1.6	°C/W
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	60	
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	105	

- Surface-mounted on FR4 board using 1 in sq pad size, 1 oz Cu.
- Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 10\ \mu\text{A}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			40		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 150^\circ\text{C}$		50	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.5		3.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-7.4		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		3.6	4.4	m Ω
		$V_{GS} = 5.0\text{ V}, I_D = 50\text{ A}$		6.5	7.8	
Forward Transconductance	gFS	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		16.8		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 12\text{ V}$		5300		pF
Output Capacitance	C_{oss}			850		
Reverse Transfer Capacitance	C_{rss}			550		
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 25\text{ V}$		5025		pF
Output Capacitance	C_{oss}			580		
Reverse Transfer Capacitance	C_{rss}			400		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 50\text{ A}$		75	100	nC
Threshold Gate Charge	$Q_{G(TH)}$			6.0		
Gate-to-Source Charge	Q_{GS}			18		
Gate-to-Drain Charge	Q_{GD}			15		

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}, I_D = 50\text{ A}, R_G = 2.0\ \Omega$		14		ns
Rise Time	t_r			52		
Turn-Off Delay Time	$t_{d(off)}$			39		
Fall Time	t_f			8.5		

- Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V},$ $I_S = 50\text{ A}$		0.9	1.2	V
		$V_{GS} = 0\text{ V},$ $I_S = 20\text{ A}$		0.8	1.0	
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V},$ $dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 50\text{ A}$		25		ns
Charge Time	t_a			15		
Discharge Time	t_b			10		
Reverse Recovery Charge	Q_{RR}			15		

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TYPICAL PERFORMANCE CHARACTERISTICS

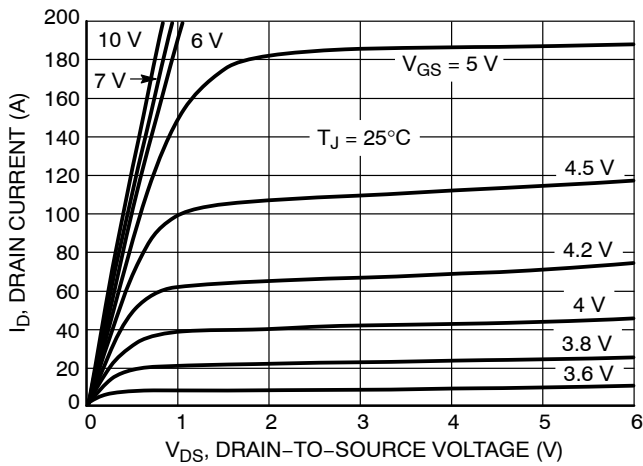


Figure 1. On-Region Characteristics

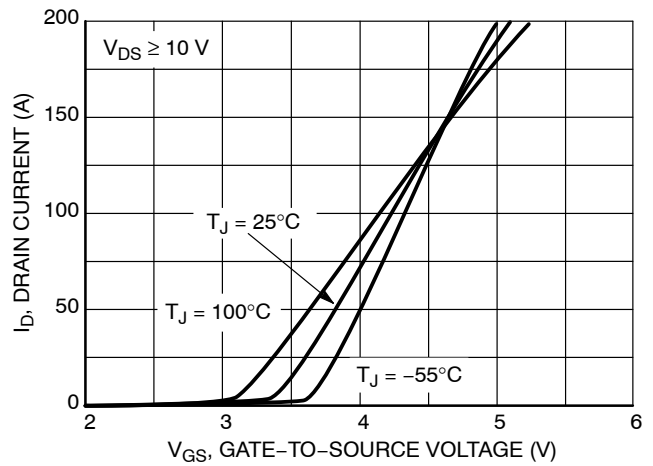


Figure 2. Transfer Characteristics

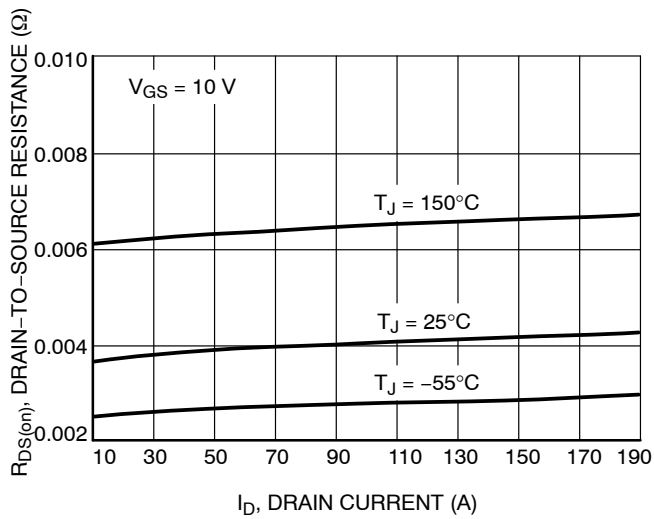


Figure 3. On-Resistance vs. Drain Current

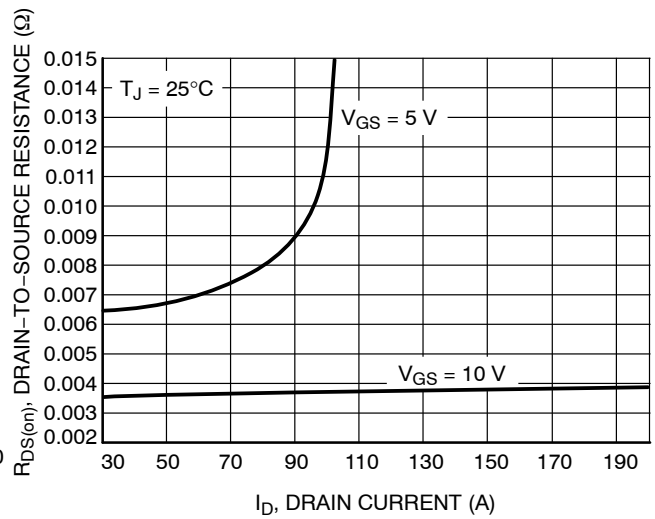


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

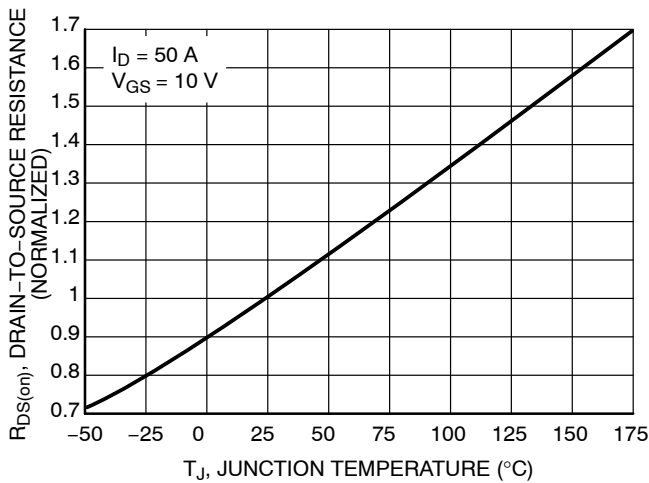


Figure 5. On-Resistance Variation with Temperature

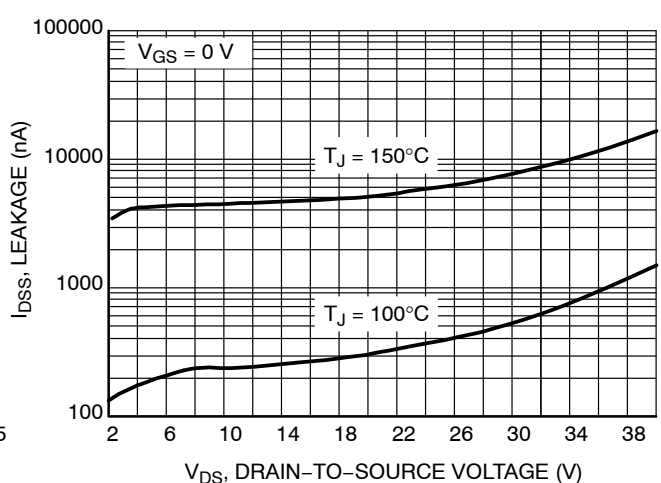


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CHARACTERISTICS

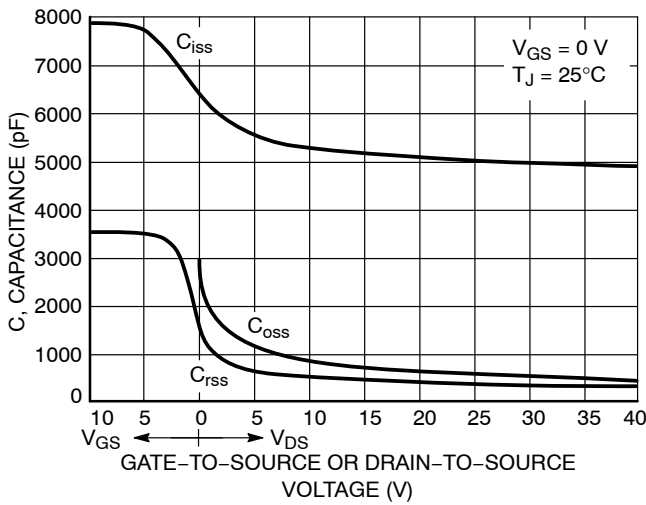


Figure 7. Capacitance Variation

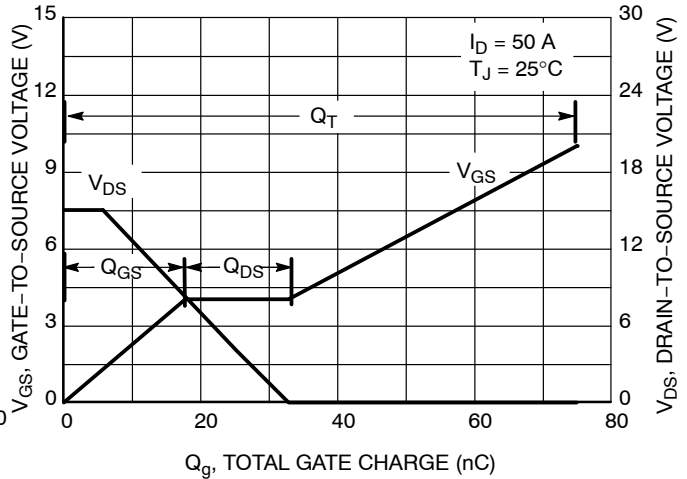


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

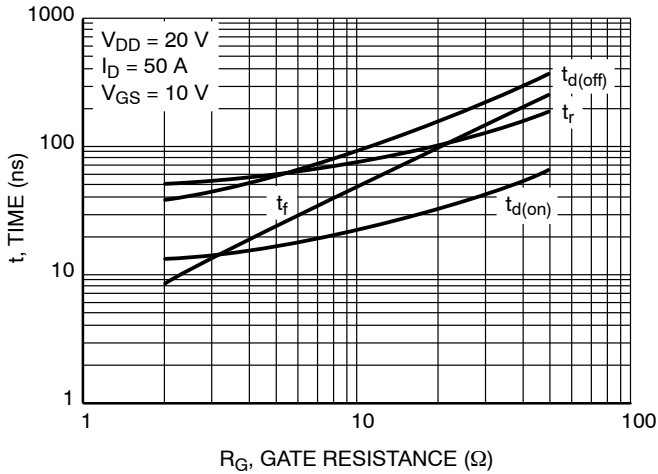


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

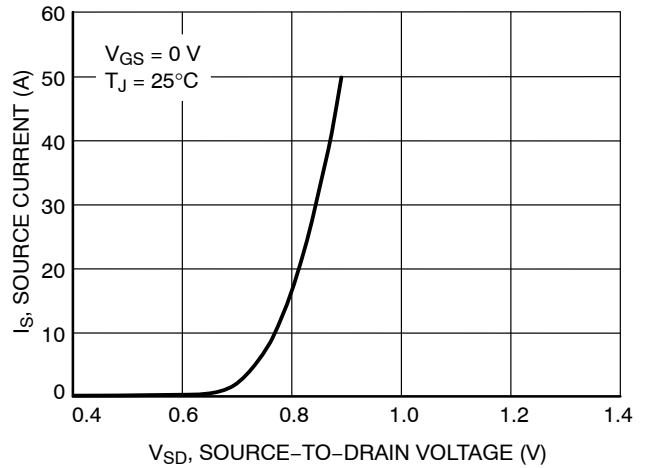


Figure 10. Diode Forward Voltage vs. Current

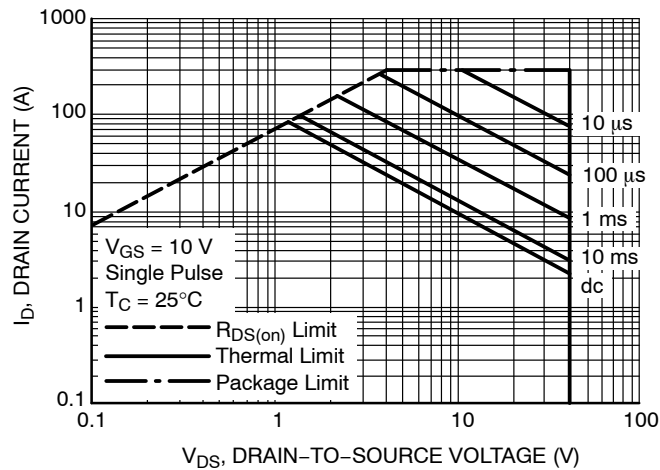


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL PERFORMANCE CHARACTERISTICS

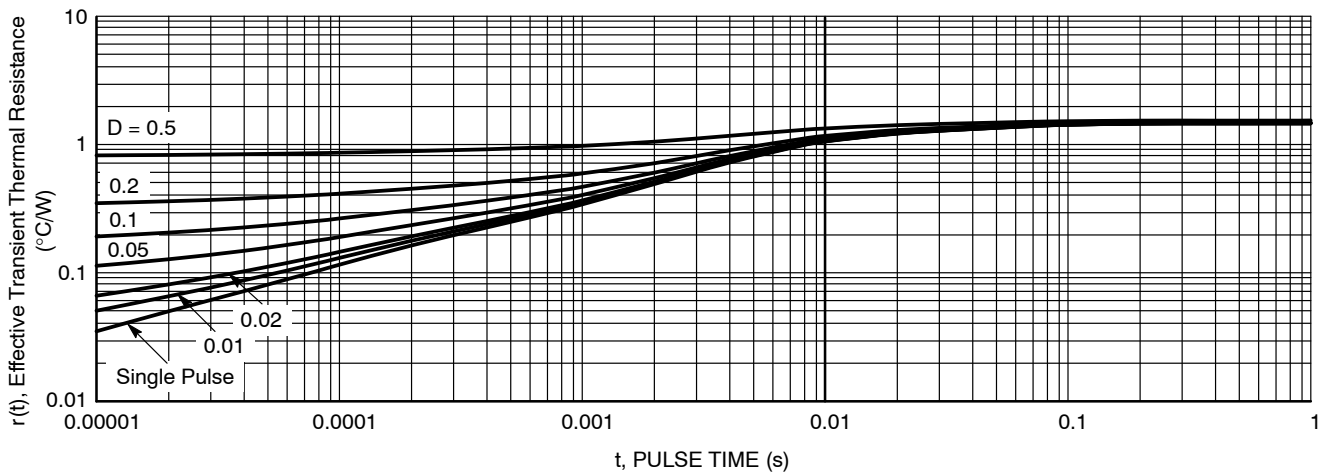


Figure 12. Thermal Response

ORDERING INFORMATION

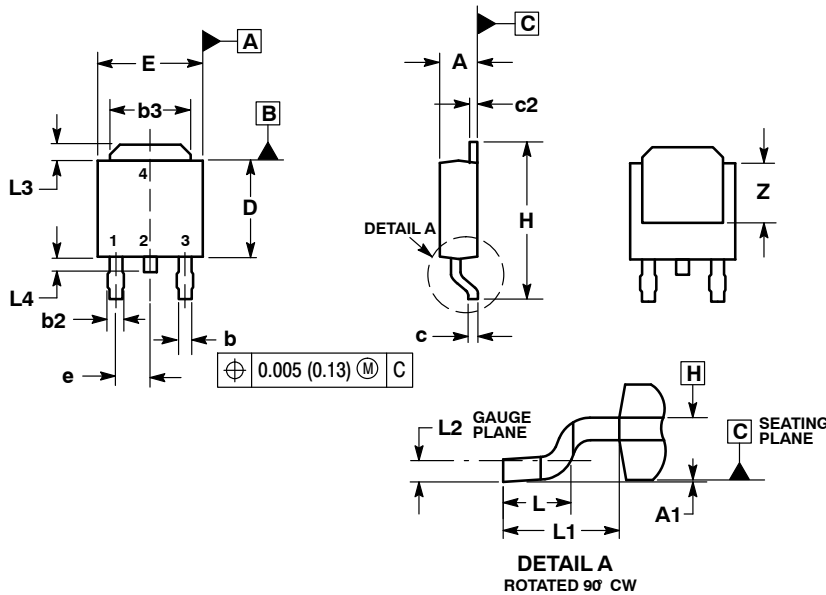
Order Number	Package	Shipping [†]
NTD5802NT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NVD5802NT4G	DPAK (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTD5802N, NVD5802N

PACKAGE DIMENSIONS

DPAK
CASE 369C-01
ISSUE D

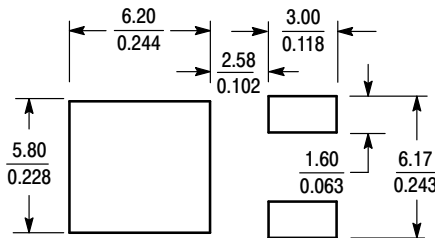


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



SCALE 3:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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